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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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2SC5852

Silicon NPN Epitaxial Planar



ADE-208-1481 (Z)

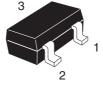
Rev.0 Feb. 2002

Features

• VHF amplifier, local oscillator

Outline

CMPAK



- 1. Emitter
- 2. Base
- 3. Collector

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Collector to base voltage	$V_{\scriptscriptstyle{CBO}}$	30	V	
Collector to emitter voltage	V _{CEO}	20	V	
Emitter to base voltage	V _{EBO}	4	V	
Collector current	I _c	20	mA	
Collector power dissipation	P _c *	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

^{*}Value on the glass epoxy board (10 mm x 10 mm x 0.7 mm)

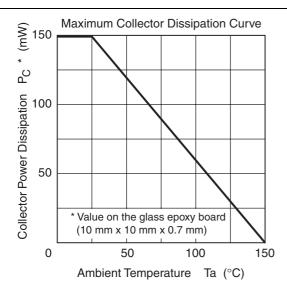
Electrical Characteristics

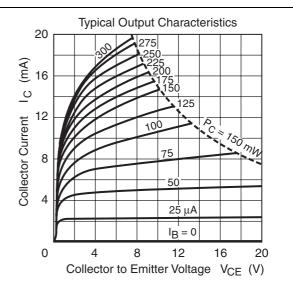
 $(Ta = 25^{\circ}C)$

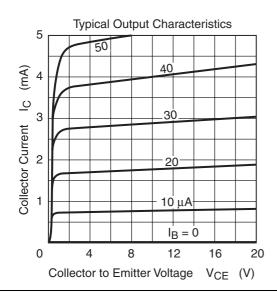
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{_{(BR)CBO}}$	30	_	_	V	$I_{c} = 10 \mu A, I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	$I_{c} = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{_{(BR)EBO}}$	4	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CEO}	_	_	0.5	μΑ	V _{CE} = 10 V, R _{BE} = ∞
Emitter cutoff current	I _{EBO}	_	_	0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	60	_	200	_	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$
Collector to emitter saturation voltage	$V_{_{\text{CE(sat)}}}$	_	0.17	_	V	$I_c = 20 \text{ mA}, I_B = 4 \text{ mA}$
Base to emitter voltage	$V_{\scriptscriptstyle BE}$	_	0.72	_	٧	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$
Gain bandwidth product	f _T		940	_	MHz	$V_{CE} = 6V$, $I_{C} = 5$ mA
Collector output capacitance	C _{ob}	_	0.9	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

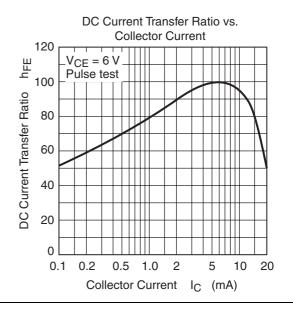
Notes: 1. The 2SC5852 is grouped by $h_{\rm FE}$ as follows.

Grade	В	С
Mark	QB	QC
h _{FE}	60 to 120	100 to 200

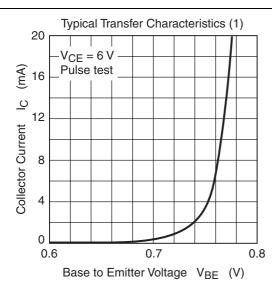


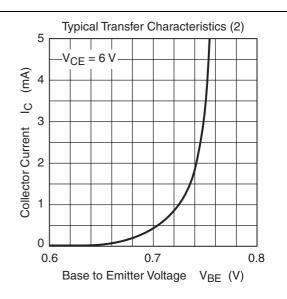


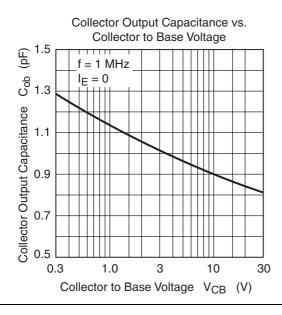


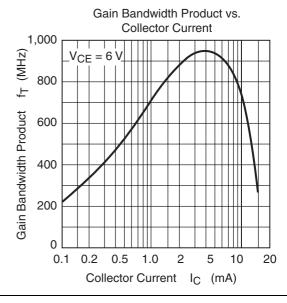


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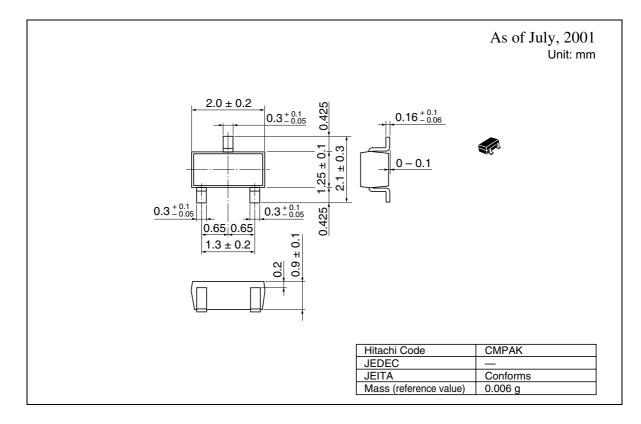








Package Dimensions



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